

isc Silicon NPN RF Transistor

2SC4249

DESCRIPTION

- Low Noise
NF = 2dB TYP. @ f = 200MHz
- High Gain
G_{pe} = 24dB TYP. @ f = 200MHz

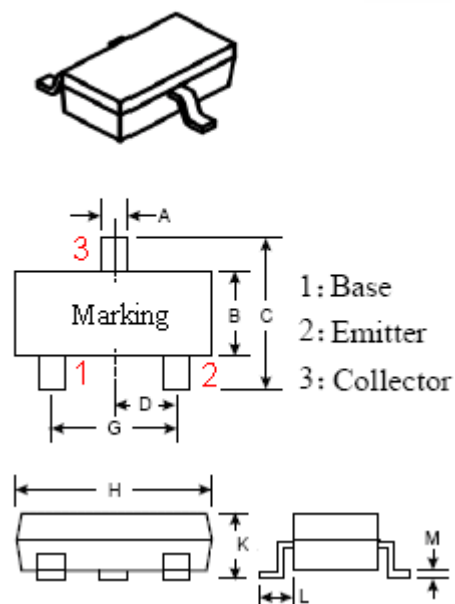
APPLICATIONS

- TV VHF RF amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3	V
I _C	Collector Current-Continuous	20	mA
I _B	Base Current-Continuous	10	mA
P _C	Collector Power Dissipation @T _C =25℃	0.1	W
T _J	Junction Temperature	125	℃
T _{stg}	Storage Temperature Range	-55~125	℃

SOT-323 package



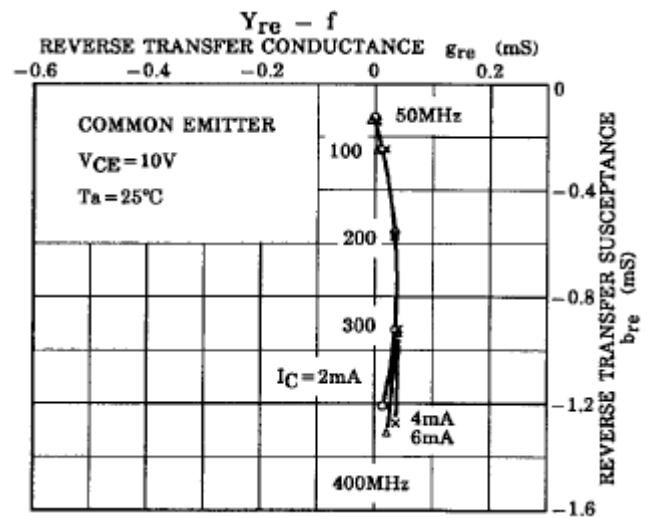
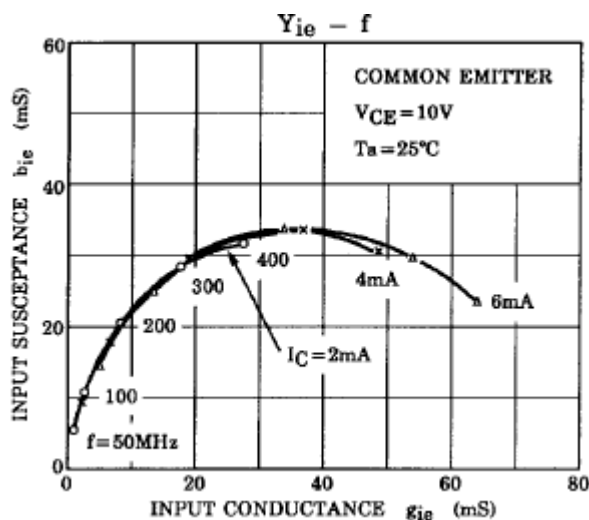
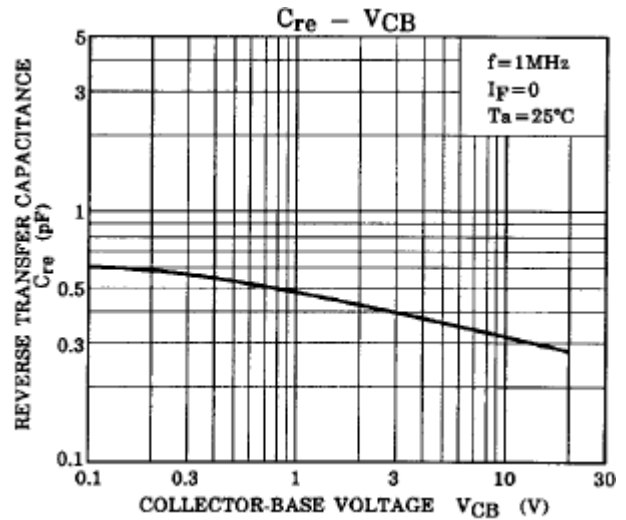
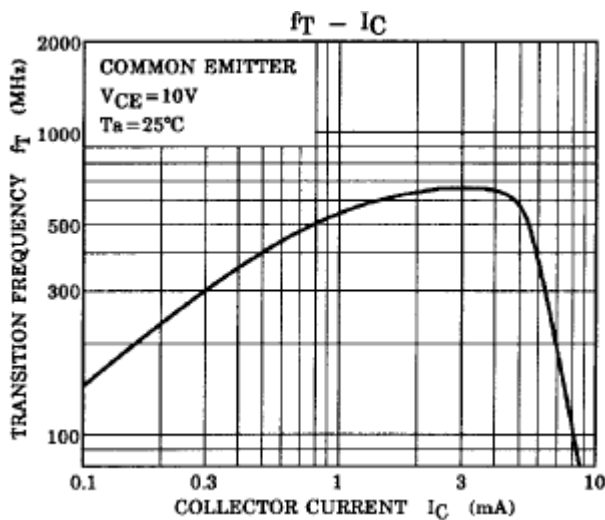
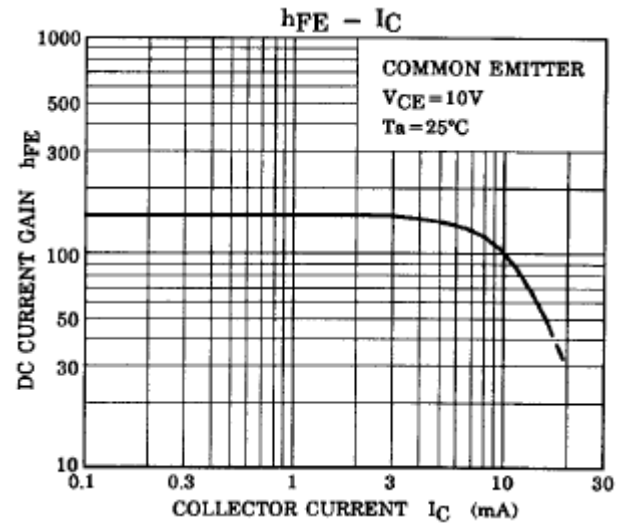
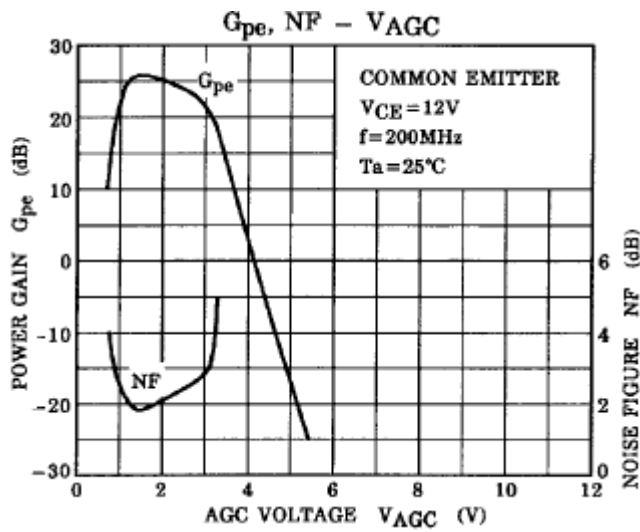
DIM	mm	
	MIN	MAX
A	0.30	0.40
B	1.15	1.35
C	2.00	2.40
D	0.65	
H	1.80	2.20
K	0.80	1.00
M	0.10	0.25

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I _{CBO}	Collector Cutoff Current	V _{CB} = 25V; I _E = 0			0.1	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 2V; I _C = 0			0.1	μ A
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA ; I _B = 0	30			V
h _{FE}	DC Current Gain	I _C = 2mA ; V _{CE} = 10V	60		300	
f _T	Current-Gain—Bandwidth Product	I _C = 2mA ; V _{CE} = 10V	400	650		MHz
C _{re}	Feed-Back Capacitance	V _{CB} = 10V; I _E = 0; f= 1.0MHz		0.35	0.5	pF
G _{pe}	Power Gain	V _{CC} = 12V; V _{AGC} = 1.4V; f= 200MHz	20	24	28	dB
NF	Noise Figure			2	3.2	dB

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